

LMH6618

130 MHz, 1.25 mA Rail-to-Rail Input and Output Operational Amplifier with Shutdown

General Description

The LMH6618 is a 130 MHz rail-to-rail input and output amplifier designed for ease of use in a wide range of applications requiring high speed, low supply current, low noise, and the ability to drive complex ADC and video loads. The operating voltage range extends from 2.7V to 11V and the supply current is typically 1.25 mA at 5V.

The amplifier's voltage feedback design topology provides balanced inputs and high open loop gain for ease of use and accuracy in applications such as active filter design. Offset voltage is typically 0.1 mV and settling time to 0.01% is 120 ns which combined with an 80 dBc SFDR at 1 MHz makes the part suitable for use as an input buffer for popular 10-bit and 12-bit mega-sample ADCs.

The input common mode range extends 200 mV beyond the supply rails. The output swings to within 270 mV of the supply rails for a 150Ω load and 83 mV of the supply rail for a 1 kΩ load providing true single supply operation and maximum signal dynamic range on low power rails. The amplifier output will source and sink 35 mA and drive up to 15 pF loads without the need for external compensation.

The LMH6618 has an active low disable pin which reduces the supply current to 72 μA and is offered in the space saving 6-Pin TSOT23 package. The LMH6618 is available with a -40°C to +125°C extended industrial temperature grade.

Features

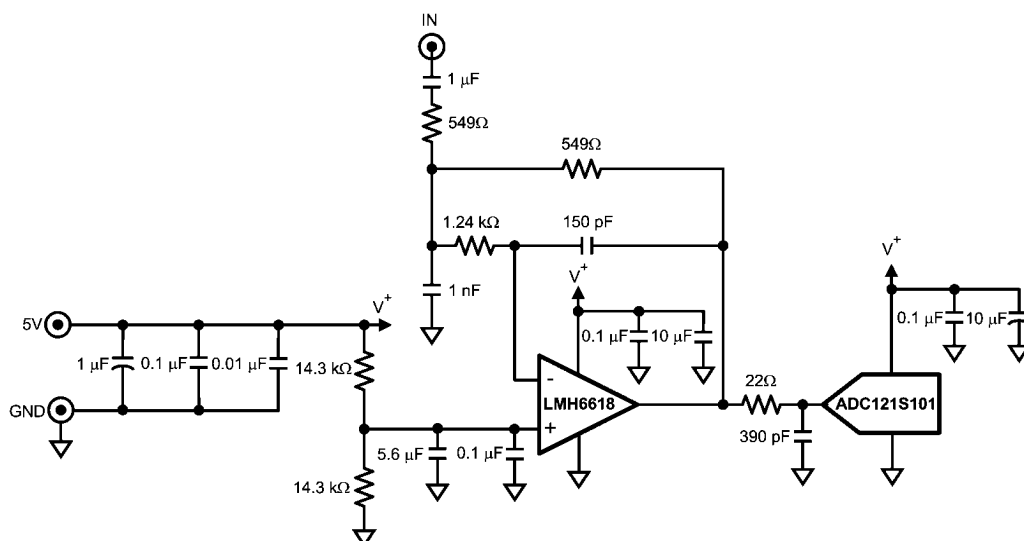
$V_S = 5V$, $R_L = 1\text{ k}\Omega$, $T_A = 25^\circ\text{C}$ and $A_V = +1$, unless otherwise specified.

- Operating voltage range 2.7V to 11V
- Supply current 1.25 mA
- Small signal bandwidth 130 MHz
- Slew rate 55 V/μs
- Settling time to 0.1% 90 ns
- Settling time to 0.01% 120 ns
- SFDR ($f = 1\text{ MHz}$, $A_V = +1$, $V_{OUT} = 2\text{ V}_{PP}$) 80 dBc
- 0.1 dB bandwidth ($A_V = +2$) 15 MHz
- Low voltage noise 10 nV/√Hz
- Industrial temperature grade -40°C to +125°C
- Rail-to-Rail input and output

Applications

- ADC driver
- DAC buffer
- Active filters
- High speed sensor amplifier
- Current sense amplifier
- Portable video
- STB, TV video amplifier

Typical Application



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Absolute Maximum Ratings (Note 1)

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If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

ESD Tolerance (Note 2)

Human Body Model

For input pins only

2000V

For all other pins

2000V

Machine Model

200V

Supply Voltage ($V_S = V^+ - V^-$)

12V

Junction Temperature (Note 3)

150°C max

Operating Ratings (Note 1)Supply Voltage ($V_S = V^+ - V^-$)

2.7V to 11V

Ambient Temperature Range (Note 3)

-40°C to +125°C

Package Thermal Resistance (θ_{JA})

6-Pin TSOT23

231°C/W

+3V Electrical Characteristics

Unless otherwise specified, all limits are guaranteed for $T_J = +25^\circ\text{C}$, $V^+ = 3\text{V}$, $V^- = 0\text{V}$, $\overline{\text{DISABLE}} = 3\text{V}$, $V_{CM} = V_O = V^+/2$, $A_V = +1$ ($R_F = 0\Omega$), otherwise $R_F = 2\text{k}\Omega$ for $A_V \neq +1$, $R_L = 1\text{k}\Omega \parallel 5\text{pF}$.

Boldface Limits apply at temperature extremes. (Note 4)

Symbol	Parameter	Condition	Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units
Frequency Domain Response						
SSBW	-3 dB Bandwidth Small Signal	$A_V = 1$, $R_L = 1\text{k}\Omega$, $V_{OUT} = 0.2 V_{PP}$		120		MHz
		$A_V = 2$, -1 , $R_L = 1\text{k}\Omega$, $V_{OUT} = 0.2 V_{PP}$		56		
GBW	Gain Bandwidth	$A_V = 10$, $R_F = 2\text{k}\Omega$, $R_G = 221\Omega$, $R_L = 1\text{k}\Omega$, $V_{OUT} = 0.2 V_{PP}$	55	71		MHz
LSBW	-3 dB Bandwidth Large Signal	$A_V = 1$, $R_L = 1\text{k}\Omega$, $V_{OUT} = 2 V_{PP}$		13		MHz
		$A_V = 2$, $R_L = 150\Omega$, $V_{OUT} = 2 V_{PP}$		13		
Peak	Peaking	$A_V = 1$, $C_L = 5\text{pF}$		1.5		dB
0.1 dBBW	0.1 dB Bandwidth	$A_V = 2$, $V_{OUT} = 0.5 V_{PP}$, $R_F = R_G = 825\Omega$		15		MHz
DG	Differential Gain	$A_V = +2$, 4.43 MHz, $0.6\text{V} < V_{OUT} < 2\text{V}$, $R_L = 150\Omega$ to $V^+/2$		0.1		%
DP	Differential Phase	$A_V = +2$, 4.43 MHz, $0.6\text{V} < V_{OUT} < 2\text{V}$, $R_L = 150\Omega$ to $V^+/2$		0.1		deg
Time Domain Response						
t_r/t_f	Rise & Fall Time	2V Step, $A_V = 1$		36		ns
SR	Slew Rate	2V Step, $A_V = 1$	36	46		V/ μs
$t_{s,0.1}$	0.1% Settling Time	2V Step, $A_V = -1$		90		ns
$t_{s,0.01}$	0.01% Settling Time	2V Step, $A_V = -1$		120		
Noise and Distortion Performance						
SFDR	Spurious Free Dynamic Range	$f_C = 100\text{kHz}$, $V_{OUT} = 2 V_{PP}$, $R_L = 1\text{k}\Omega$		100		dBc
		$f_C = 1\text{MHz}$, $V_{OUT} = 2 V_{PP}$, $R_L = 1\text{k}\Omega$		80		
		$f_C = 5\text{MHz}$, $V_{OUT} = 2 V_{PP}$, $R_L = 1\text{k}\Omega$		58		
e_n	Input Voltage Noise	$f = 100\text{kHz}$		10		$\text{nV}/\sqrt{\text{Hz}}$
i_n	Input Current Noise	$f = 100\text{kHz}$		1		$\text{pA}/\sqrt{\text{Hz}}$
Input, DC Performance						
V_{OS}	Input Offset Voltage	$V_{CM} = 0.5\text{V}$ (pnp active) $V_{CM} = 2.5\text{V}$ (nnp active)		0.1	± 0.6 ± 1.0	mV
TCV_{OS}	Input Offset Voltage Average Drift	(Note 5)		0.8		$\mu\text{V}/^\circ\text{C}$
I_B	Input Bias Current	$V_{CM} = 0.5\text{V}$ (pnp active)		-1.4	-2.6	μA
		$V_{CM} = 2.5\text{V}$ (nnp active)		+1.0	+1.8	
I_O	Input Offset Current			0.01	± 0.27	μA
C_{IN}	Input Capacitance			1.5		pF
R_{IN}	Input Resistance			8		M Ω

Symbol	Parameter	Condition	Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units
CMVR	Input Voltage Range	DC, CMRR \geq 65 dB	-0.2		3.2	V
CMRR	Common Mode Rejection Ratio	V_{CM} Stepped from -0.1V to 1.4V	78	96		dB
		V_{CM} Stepped from 2.0V to 3.1V	81	107		
A_{OL}	Open Loop Gain	$R_L = 1\text{ k}\Omega$ to $V+/2$		98		dB
		$R_L = 150\Omega$ to $V+/2$		82		
Output DC Characteristics						
V_O	Output Swing High (Voltage from $V+$ Supply Rail)	$R_L = 1\text{ k}\Omega$ to $V+/2$	56 62	50		mV
		$R_L = 150\Omega$ to $V+/2$	172 198	160		
	Output Swing Low (Voltage from $V-$ Supply Rail)	$R_L = 1\text{ k}\Omega$ to $V+/2$		60	66 74	
		$R_L = 150\Omega$ to $V+/2$		170	184 217	
		$R_L = 150\Omega$ to $V-$		29	39 43	
I_{OUT}	Linear Output Current	$V_{OUT} = V+/2$ (Note 6)	± 25	± 35		mA
R_O	Output Resistance	$f = 1\text{ MHz}$		0.17		Ω
Enable Pin Operation						
	Enable High Voltage Threshold	Enabled	2.0			V
	Enable Pin High Current	$V_{DISABLE} = 3V$		0.04		μA
	Enable Low Voltage Threshold	Disabled			1.0	V
	Enable Pin Low Current	$V_{DISABLE} = 0V$		1		μA
T_{on}	Turn-On Time			25		ns
T_{off}	Turn-Off Time			90		ns
Power Supply Performance						
PSRR	Power Supply Rejection Ratio	DC, $V_{CM} = 0.5V$, $V_S = 2.7V$ to $11V$	84	104		dB
I_S	Supply Current	$R_L = \infty$		1.2	1.5 1.7	mA
I_{SD}	Disable Shutdown Current	$DISABLE = 0V$		59	85	μA
<p>+5V Electrical Characteristics Unless otherwise specified, all limits are guaranteed for $T_J = +25^\circ C$, $V+ = 5V$, $V- = 0V$, $DISABLE = 5V$, $V_{CM} = V_O = V+/2$, $A_V = +1$ ($R_F = 0\Omega$), otherwise $R_F = 2\text{ k}\Omega$ for $A_V \neq +1$, $R_L = 1\text{ k}\Omega$ 5 pF. Boldface Limits apply at temperature extremes.</p>						
Symbol	Parameter	Condition	Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units
Frequency Domain Response						
SSBW	-3 dB Bandwidth Small Signal	$A_V = 1$, $R_L = 1\text{ k}\Omega$, $V_{OUT} = 0.2 V_{PP}$		130		MHz
		$A_V = 2$, -1 , $R_L = 1\text{ k}\Omega$, $V_{OUT} = 0.2 V_{PP}$		53		
GBW	Gain Bandwidth	$A_V = 10$, $R_F = 2\text{ k}\Omega$, $R_G = 221\Omega$, $R_L = 1\text{ k}\Omega$, $V_{OUT} = 0.2 V_{PP}$	54	64		MHz
LSBW	-3 dB Bandwidth Large Signal	$A_V = 1$, $R_L = 1\text{ k}\Omega$, $V_{OUT} = 2 V_{PP}$		15		MHz
		$A_V = 2$, $R_L = 150\Omega$, $V_{OUT} = 2 V_{PP}$		15		
Peak	Peaking	$A_V = 1$, $C_L = 5\text{ pF}$		0.5		dB
0.1 dBBW	0.1 dB Bandwidth	$A_V = 2$, $V_{OUT} = 0.5 V_{PP}$, $R_F = R_G = 1\text{ k}\Omega$		15		MHz
DG	Differential Gain	$A_V = +2$, 4.43 MHz, $0.6V < V_{OUT} < 2V$, $R_L = 150\Omega$ to $V+/2$		0.1		%

Symbol	Parameter	Condition	Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units
DP	Differential Phase	$A_V = +2$, 4.43 MHz, $0.6V < V_{OUT} < 2V$, $R_L = 150\Omega$ to $V+/2$		0.1		deg
Time Domain Response						
t_r/t_f	Rise & Fall Time	2V Step, $A_V = 1$		30		ns
SR	Slew Rate	2V Step, $A_V = 1$	44	55		V/ μ s
$t_{s,0.1}$	0.1% Settling Time	2V Step, $A_V = -1$		90		ns
$t_{s,0.01}$	0.01% Settling Time	2V Step, $A_V = -1$		120		
Distortion and Noise Performance						
SFDR	Spurious Free Dynamic Range	$f_C = 100$ kHz, $V_{OUT} = 2 V_{PP}$, $R_L = 1$ k Ω		100		dBc
		$f_C = 1$ MHz, $V_{OUT} = 2 V_{PP}$, $R_L = 1$ k Ω		80		
		$f_C = 5$ MHz, $V_O = 2 V_{PP}$, $R_L = 1$ k Ω		58		
e_n	Input Voltage Noise	$f = 100$ kHz		10		nV/ \sqrt{Hz}
i_n	Input Current Noise	$f = 100$ kHz		1		pA/ \sqrt{Hz}
Input, DC Performance						
V_{OS}	Input Offset Voltage	$V_{CM} = 0.5V$ (pnp active) $V_{CM} = 4.5V$ (nnp active)		0.1	± 0.6 ± 1.0	mV
TCV_{OS}	Input Offset Voltage Average Drift	(Note 5)		0.8		$\mu V/^\circ C$
I_B	Input Bias Current	$V_{CM} = 0.5V$ (pnp active)		-1.5	-2.4	μA
		$V_{CM} = 4.5V$ (nnp active)		+1.0	+1.9	
I_O	Input Offset Current			0.01	± 0.26	μA
C_{IN}	Input Capacitance			1.5		pF
R_{IN}	Input Resistance			8		M Ω
CMVR	Input Voltage Range	DC, CMRR ≥ 65 dB	-0.2		5.2	V
CMRR	Common Mode Rejection Ratio	V_{CM} Stepped from -0.1V to 3.4V	81	98		dB
		V_{CM} Stepped from 4.0V to 5.1V	84	108		
AOL	Open Loop Gain	$R_L = 1$ k Ω to $V+/2$		100		dB
		$R_L = 150\Omega$ to $V+/2$		83		
Output DC Characteristics						
V_O	Output Swing High (Voltage from $V+$ Supply Rail)	$R_L = 1$ k Ω to $V+/2$	73 82	60		mV
		$R_L = 150\Omega$ to $V+/2$	255 295	230		
	Output Swing Low (Voltage from $V-$ Supply Rail)	$R_L = 1$ k Ω to $V+/2$		75	83 96	
		$R_L = 150\Omega$ to $V+/2$		250	270 321	
		$R_L = 150\Omega$ to $V-$		32	43 45	
	I_{OUT}	Linear Output Current	$V_{OUT} = V+/2$ (Note 6)	± 25	± 35	
R_O	Output Resistance	$f = 1$ MHz		0.17		Ω
Enable Pin Operation						
	Enable High Voltage Threshold	Enabled	3.0			V
	Enable Pin High Current	$V_{DISABLE} = 5V$		1.2		μA
	Enable Low Voltage Threshold	Disabled			2.0	V
	Enable Pin Low Current	$V_{DISABLE} = 0V$		2.5		μA
T_{on}	Turn-On Time			25		ns
T_{off}	Turn-Off Time			90		ns

Symbol	Parameter	Condition	Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units
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Power Supply Performance						
PSRR	Power Supply Rejection Ratio	DC, $V_{CM} = 0.5V$, $V_S = 2.7V$ to $11V$	84	104		dB
I_S	Supply Current	$R_L = \infty$		1.25	1.5 1.7	mA
I_{SD}	Disable Shutdown Current	$\overline{DISABLE} = 0V$		72	105	μA
$\pm 5V$ Electrical Characteristics Unless otherwise specified, all limits are guaranteed for $T_J = +25^\circ C$, $V_+ = 5V$, $V_- = -5V$, $\overline{DISABLE} = 5V$, $V_{CM} = V_O = 0V$, $A_V = +1$ ($R_F = 0\Omega$), otherwise $R_F = 2\text{ k}\Omega$ for $A_V \neq +1$, $R_L = 1\text{ k}\Omega \parallel 5\text{ pF}$. Boldface Limits apply at temperature extremes.						
Symbol	Parameter	Condition	Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units
Frequency Domain Response						
SSBW	-3 dB Bandwidth Small Signal	$A_V = 1$, $R_L = 1\text{ k}\Omega$, $V_{OUT} = 0.2 V_{PP}$		140		MHz
		$A_V = 2$, -1 , $R_L = 1\text{ k}\Omega$, $V_{OUT} = 0.2 V_{PP}$		53		
GBW	Gain Bandwidth	$A_V = 10$, $R_F = 2\text{ k}\Omega$, $R_G = 221\Omega$, $R_L = 1\text{ k}\Omega$, $V_{OUT} = 0.2 V_{PP}$	54	65		MHz
LSBW	-3 dB Bandwidth Large Signal	$A_V = 1$, $R_L = 1\text{ k}\Omega$, $V_{OUT} = 2 V_{PP}$		16		MHz
		$A_V = 2$, $R_L = 150\Omega$, $V_{OUT} = 2 V_{PP}$		15		
Peak	Peaking	$A_V = 1$, $C_L = 5\text{ pF}$		0.05		dB
0.1 dBBW	0.1 dB Bandwidth	$A_V = 2$, $V_{OUT} = 0.5 V_{PP}$, $R_F = R_G = 1.21\text{ k}\Omega$		15		MHz
DG	Differential Gain	$A_V = +2$, 4.43 MHz, $0.6V < V_{OUT} < 2V$, $R_L = 150\Omega$ to $V^+/2$		0.1		%
DP	Differential Phase	$A_V = +2$, 4.43 MHz, $0.6V < V_{OUT} < 2V$, $R_L = 150\Omega$ to $V^+/2$		0.1		deg
Time Domain Response						
t_r/t_f	Rise & Fall Time	2V Step, $A_V = 1$		30		ns
SR	Slew Rate	2V Step, $A_V = 1$	45	57		V/ μs
$t_{s,0.1}$	0.1% Settling Time	2V Step, $A_V = -1$		90		ns
$t_{s,0.01}$	0.01% Settling Time	2V Step, $A_V = -1$		120		
Noise and Distortion Performance						
SFDR	Spurious Free Dynamic Range	$f_C = 100\text{ kHz}$, $V_{OUT} = 2 V_{PP}$, $R_L = 1\text{ k}\Omega$		100		dBc
		$f_C = 1\text{ MHz}$, $V_{OUT} = 2 V_{PP}$, $R_L = 1\text{ k}\Omega$		80		
		$f_C = 5\text{ MHz}$, $V_{OUT} = 2 V_{PP}$, $R_L = 1\text{ k}\Omega$		58		
e_n	Input Voltage Noise	$f = 100\text{ kHz}$		10		nV/\sqrt{Hz}
i_n	Input Current Noise	$f = 100\text{ kHz}$		1		pA/\sqrt{Hz}
Input DC Performance						
V_{OS}	Input Offset Voltage	$V_{CM} = -4.5V$ (pnp active) $V_{CM} = 4.5V$ (nnp active)		0.1	± 0.6 ± 1.0	mV
TCV_{OS}	Input Offset Voltage Average Drift	(Note 5)		0.9		$\mu V/^\circ C$
I_B	Input Bias Current	$V_{CM} = -4.5V$ (pnp active)		-1.5	-2.4	μA
		$V_{CM} = 4.5V$ (nnp active)		+1.0	+1.9	
I_O	Input Offset Current			0.01	± 0.26	μA
C_{IN}	Input Capacitance			1.5		pF
R_{IN}	Input Resistance			8		M Ω
CMVR	Input Voltage Range	DC, $CMRR \geq 65\text{ dB}$	-5.2		5.2	V

Symbol	Parameter	Condition	Min (Note 8)	Typ (Note 7)	Max (Note 8)	Units
CMRR	Common Mode Rejection Ratio	V_{CM} Stepped from $-5.1V$ to $3.4V$	84	100		dB
		V_{CM} Stepped from $4.0V$ to $5.1V$	83	108		
A_{OL}	Open Loop Gain	$R_L = 1\text{ k}\Omega$ to $V+/2$		95		dB
		$R_L = 150\Omega$ to $V+/2$		84		
Output DC Characteristics						
V_O	Output Swing High (Voltage from $V+$ Supply Rail)	$R_L = 1\text{ k}\Omega$ to GND	111 126	100		mV
		$R_L = 150\Omega$ to GND	457 526	430		
	Output Swing Low (Voltage from $V-$ Supply Rail)	$R_L = 1\text{ k}\Omega$ to GND		110	121 136	
		$R_L = 150\Omega$ to GND		440	474 559	
		$R_L = 150\Omega$ to $V-$		35	51 52	
I_{OUT}	Linear Output Current	$V_{OUT} = V+/2$ (Note 6)	± 25	± 35		mA
R_O	Output Resistance	$f = 1\text{ MHz}$		0.17		Ω
Enable Pin Operation						
	Enable High Voltage Threshold	Enabled	5.5			V
	Enable Pin High Current	$V_{DISABLE} = +5V$		16		μA
	Enable Low Voltage Threshold	Disabled			4.5	V
	Enable Pin Low Current	$V_{DISABLE} = -5V$		17		μA
T_{on}	Turn-On Time			25		ns
T_{off}	Turn-Off Time			90		ns
Power Supply Performance						
PSRR	Power Supply Rejection Ratio	DC, $V_{CM} = -4.5V$, $V_S = 2.7V$ to $11V$	84	104		dB
I_S	Supply Current	$R_L = \infty$		1.35	1.6 1.9	mA
I_{SD}	Disable Shutdown Current	$\overline{DISABLE} = -5V$		103	140	μA

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.

Note 2: Human Body Model, applicable std. MIL-STD-883, Method 3015.7. Machine Model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC) Field-Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC).

Note 3: The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A) / \theta_{JA}$. All numbers apply for packages soldered directly onto a PC Board.

Note 4: Boldface limits apply to temperature range of $-40^\circ C$ to $125^\circ C$

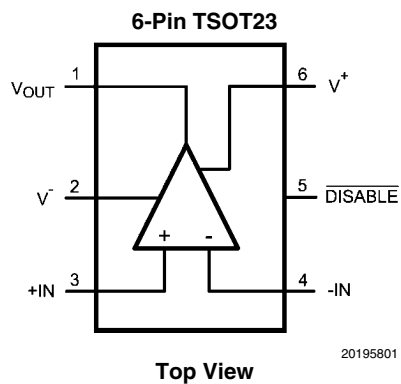
Note 5: Voltage average drift is determined by dividing the change in V_{OS} by temperature change.

Note 6: Do not short circuit the output. Continuous source or sink currents larger than the I_{OUT} typical are not recommended as it may damage the part.

Note 7: Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.

Note 8: Limits are 100% production tested at $25^\circ C$. Limits over the operating temperature range are guaranteed through correlations using the Statistical Quality Control (SQC) method.

Connection Diagram



Ordering Information

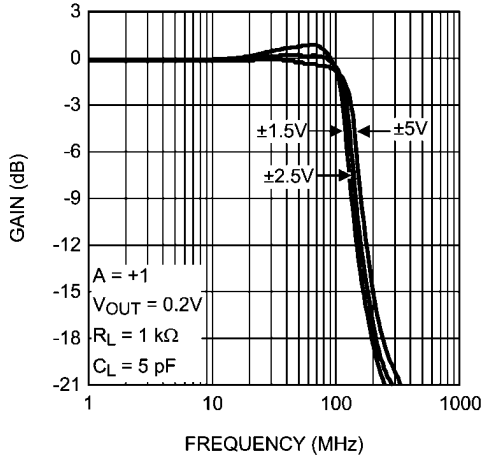
Package	Part Number	Package Marking	Transport Media	NSC Drawing
6-Pin TSOT23	LMH6618MK	AE4A	1k Units Tape and Reel	MK06A
	LMH6618MKX		3k Units Tape and Reel	

Typical Performance Characteristics

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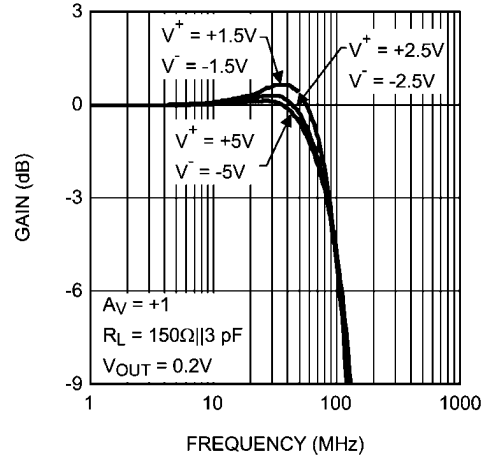
At $T_J = 25^\circ\text{C}$, $A_V = +1$ ($R_F = 0\Omega$), otherwise $R_F = 2\text{ k}\Omega$ for $A_V \neq +1$,

Closed Loop Frequency Response for Various Supplies



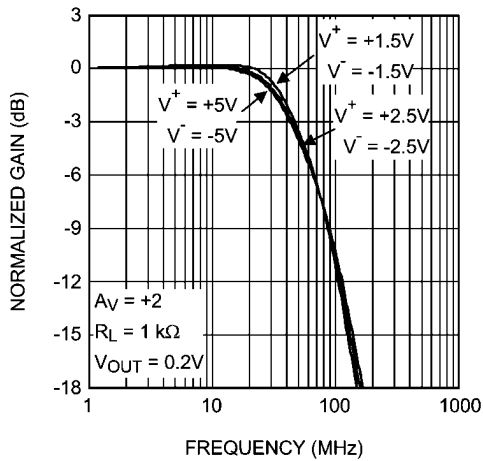
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Closed Loop Frequency Response for Various Supplies



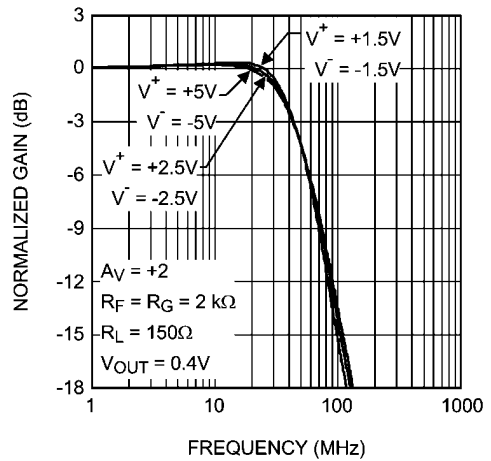
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Closed Loop Frequency Response for Various Supplies



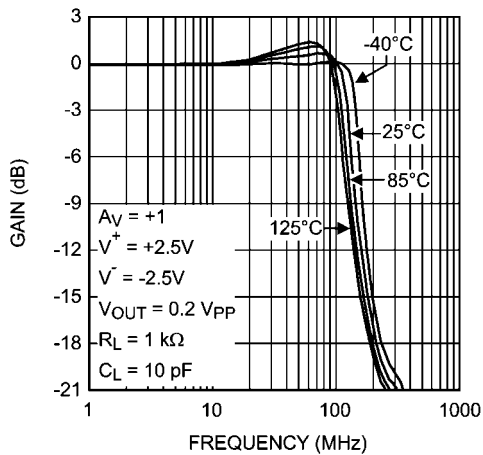
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Closed Loop Frequency Response for Various Supplies



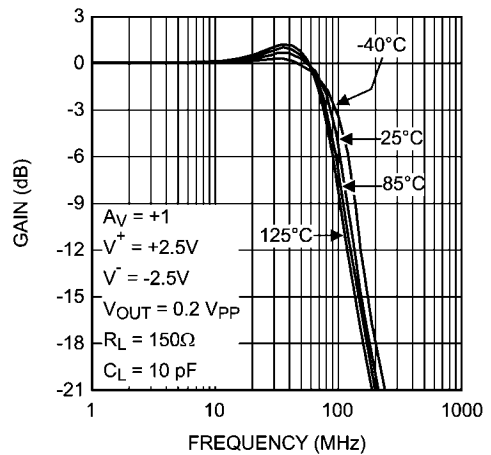
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Closed Loop Frequency Response for Various Temperatures



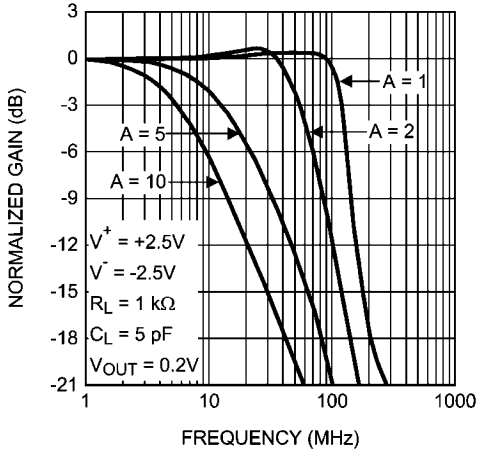
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Closed Loop Frequency Response for Various Temperatures



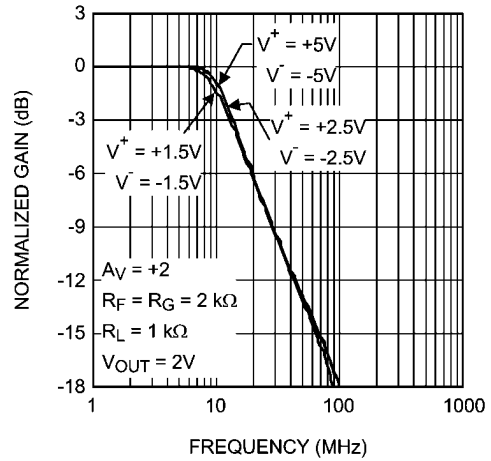
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Closed Loop Gain vs. Frequency for
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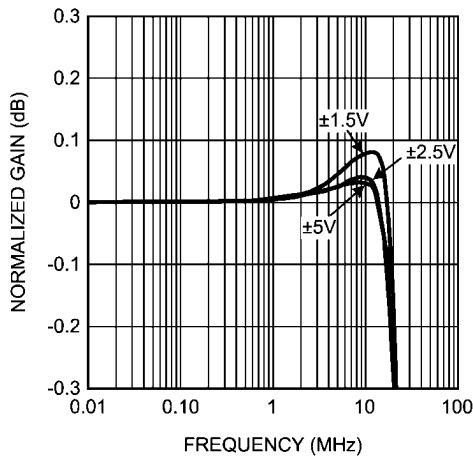
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Large Signal Frequency Response



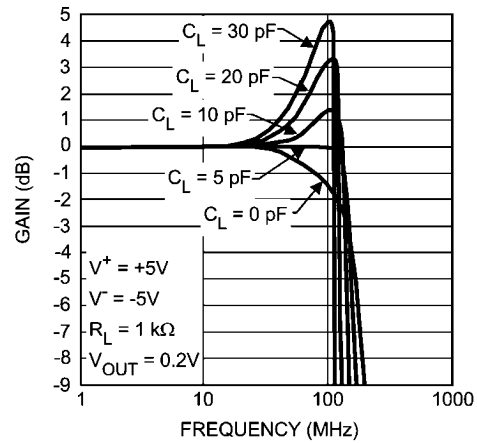
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± 0.1 dB Gain Flatness for Various Supplies



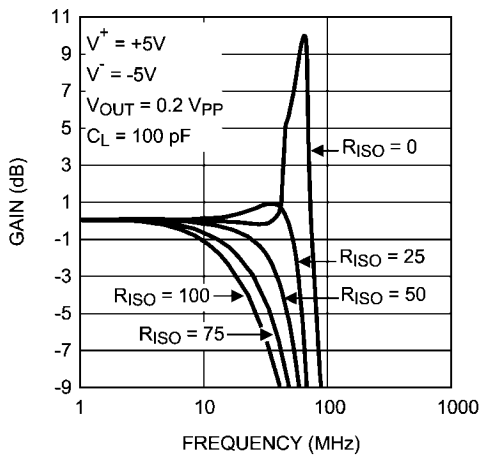
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Small Signal Frequency Response with Various Capacitive Load



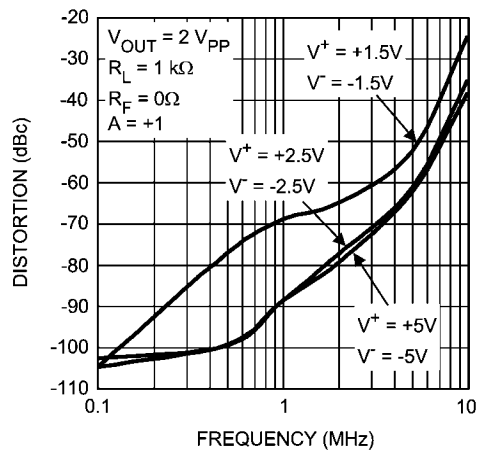
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Small Signal Frequency Response with Capacitive Load and Various R_{ISO}



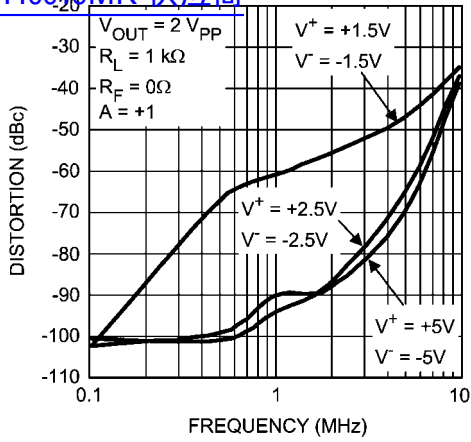
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HD2 vs. Frequency and Supply Voltage



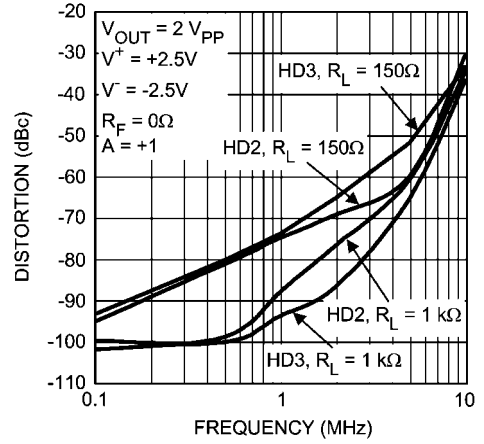
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HD3 vs. Frequency and Supply Voltage
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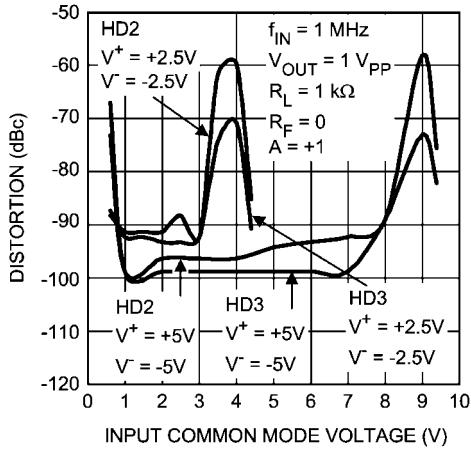
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HD2 and HD3 vs. Frequency and Load



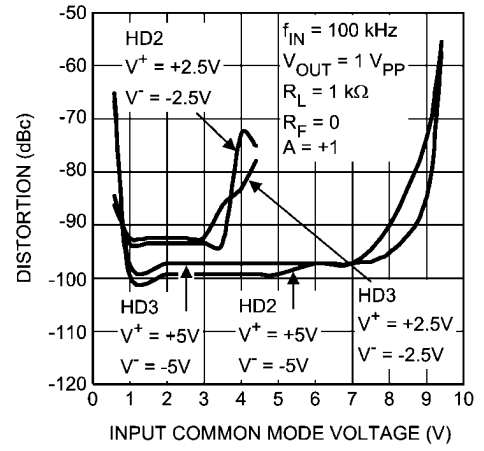
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HD2 and HD3 vs. Common Mode Voltage



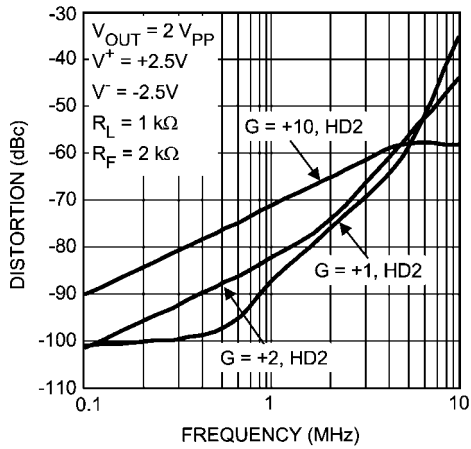
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HD2 and HD3 vs. Common Mode Voltage



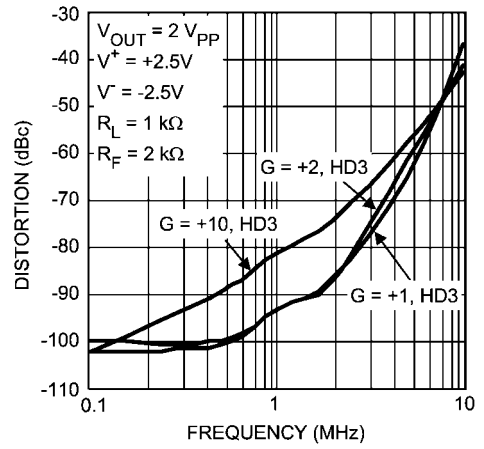
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HD2 vs. Frequency and Gain

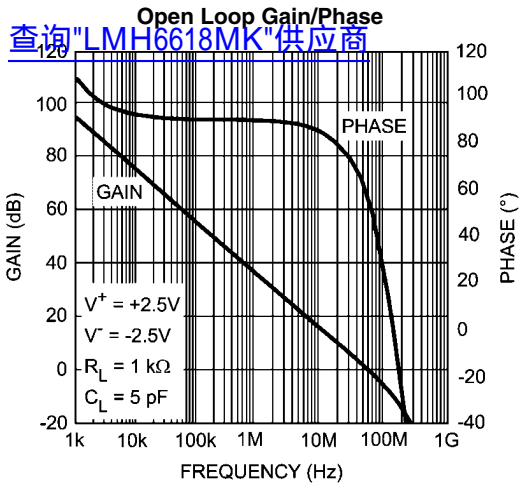


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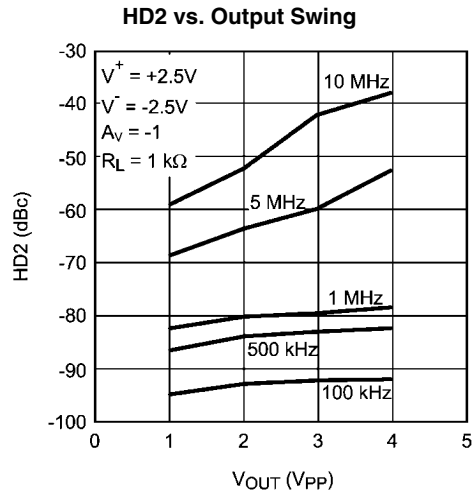
HD3 vs. Frequency and Gain



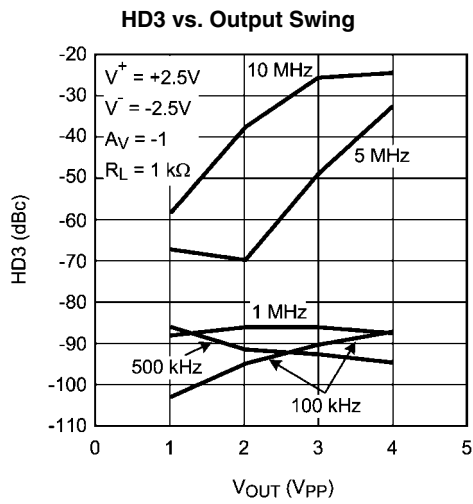
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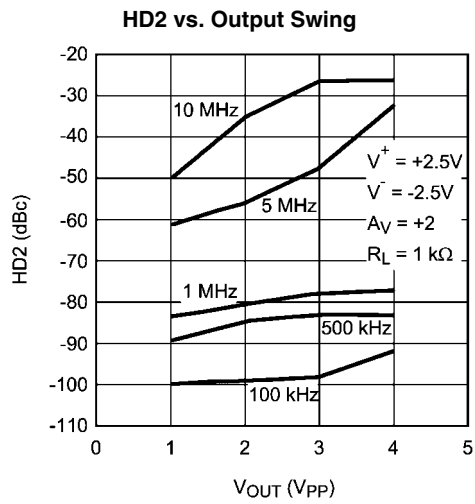
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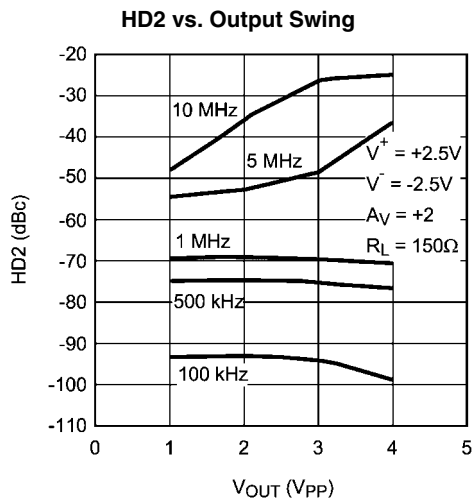
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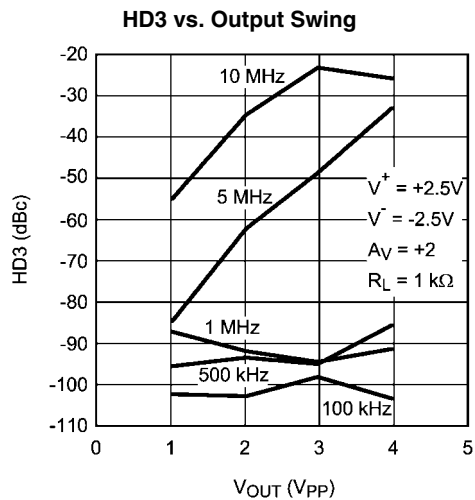
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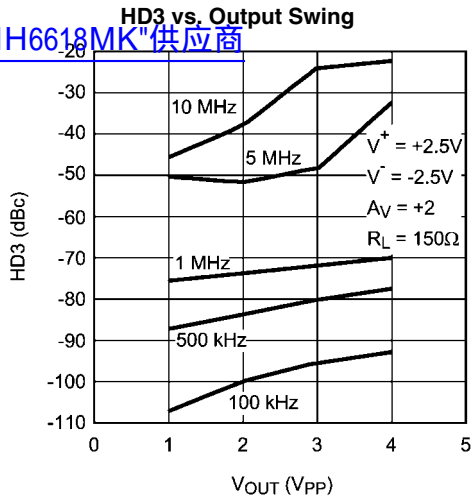


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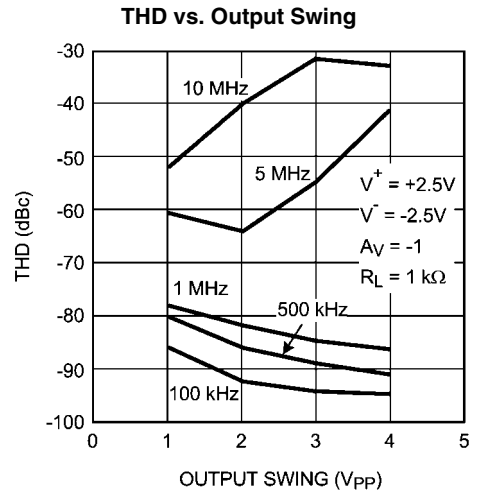


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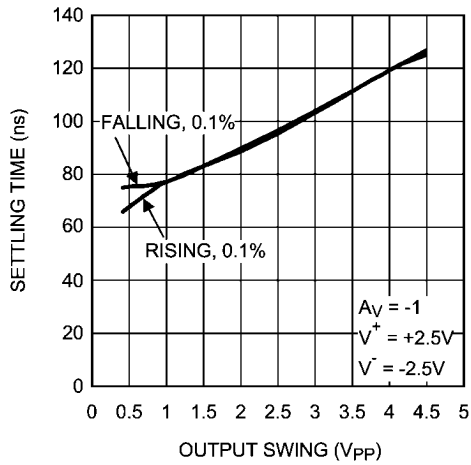


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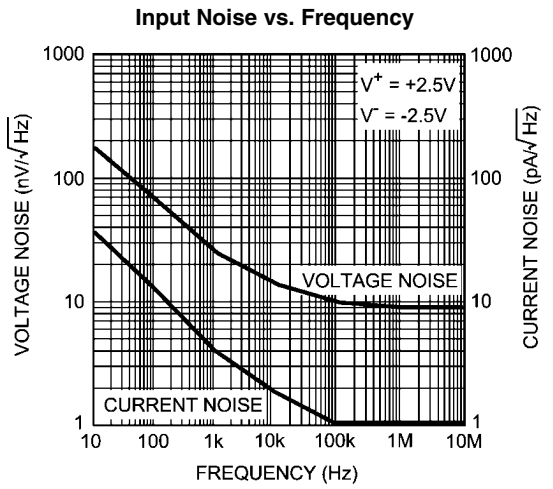


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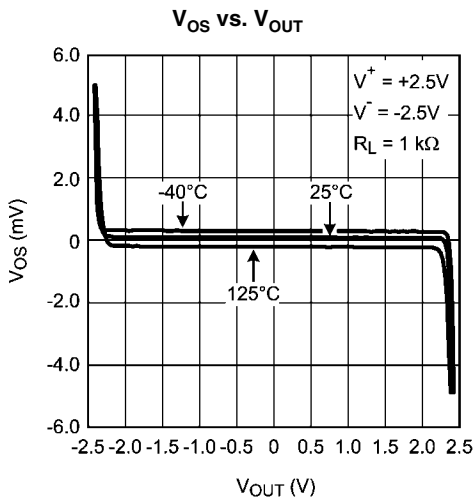
Settling Time vs. Input Step Amplitude (Output Slew and Settle Time)



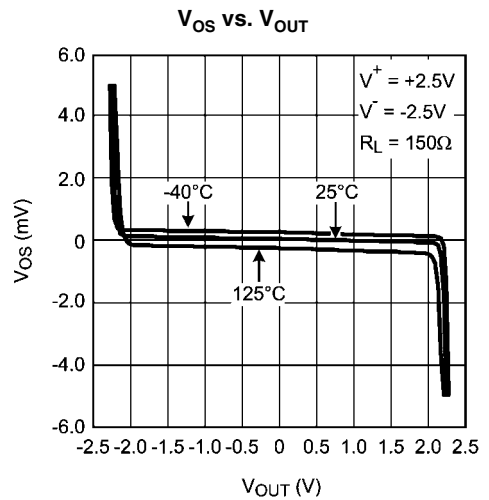
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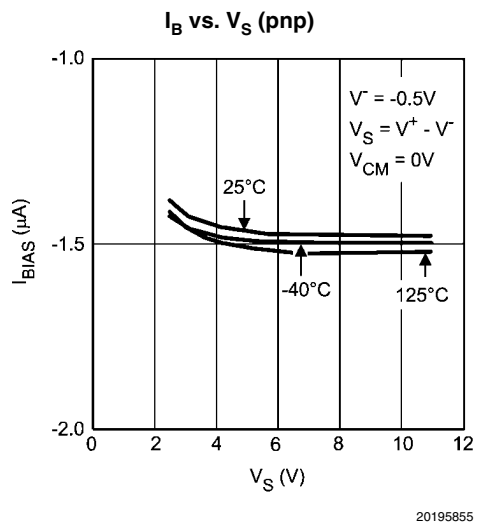
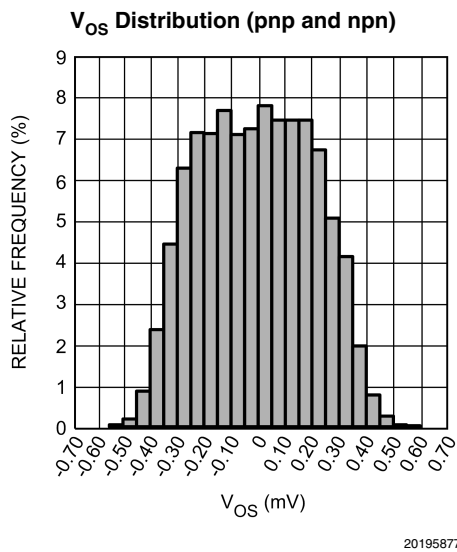
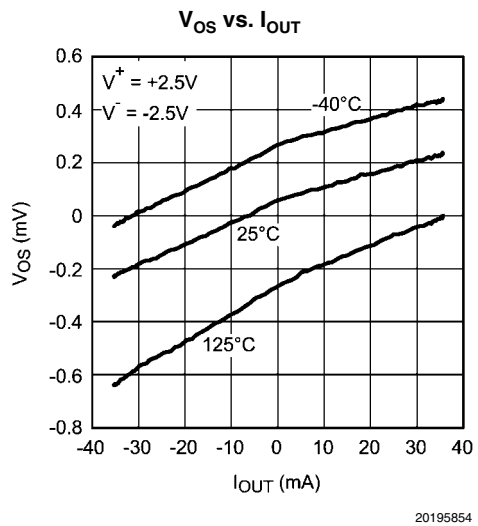
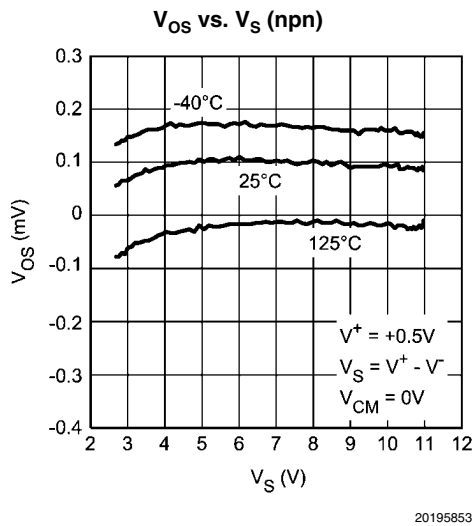
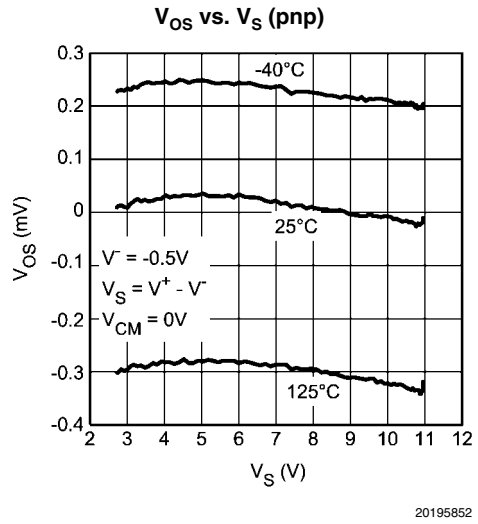
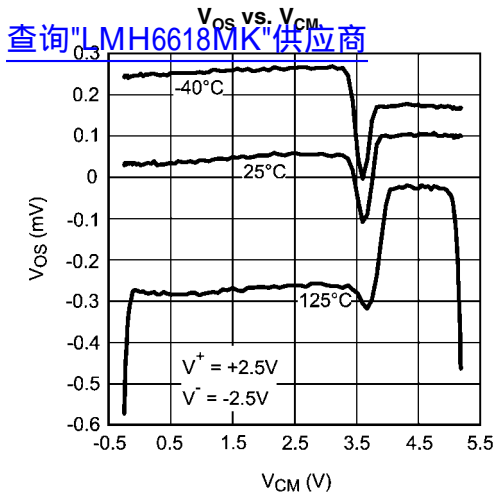
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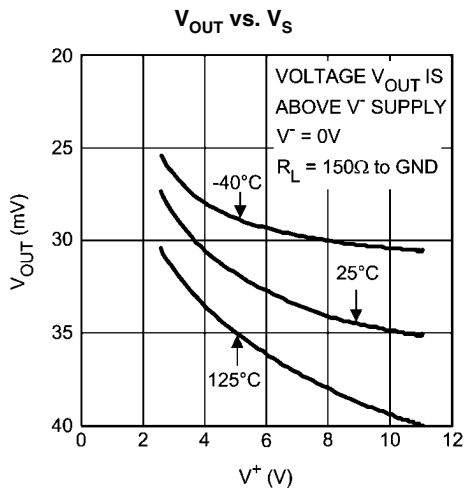
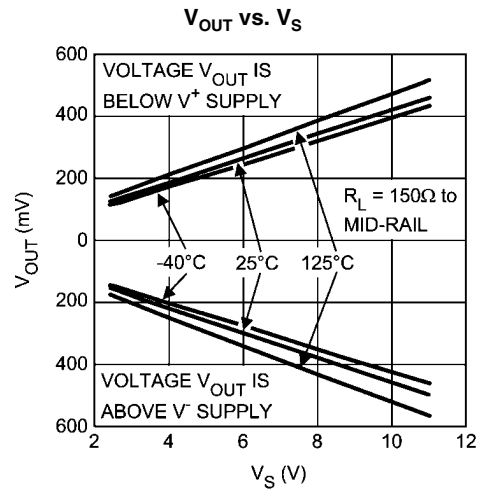
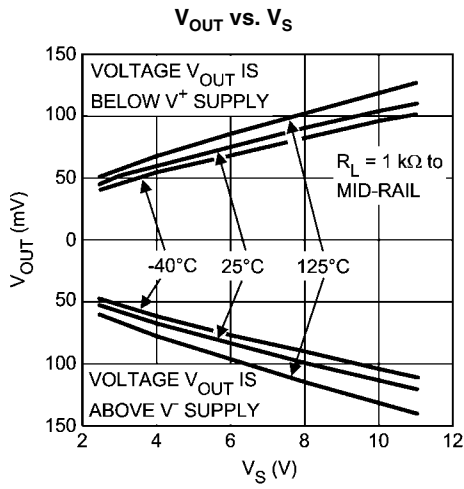
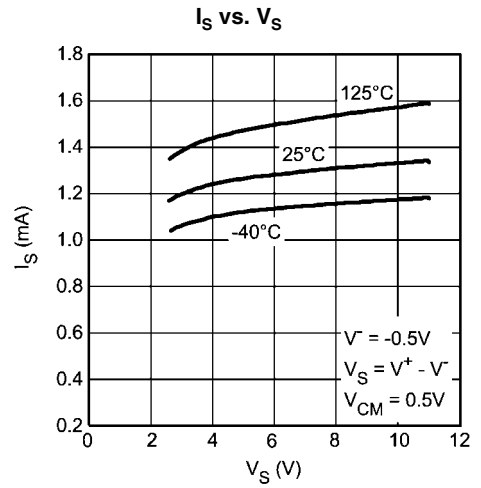
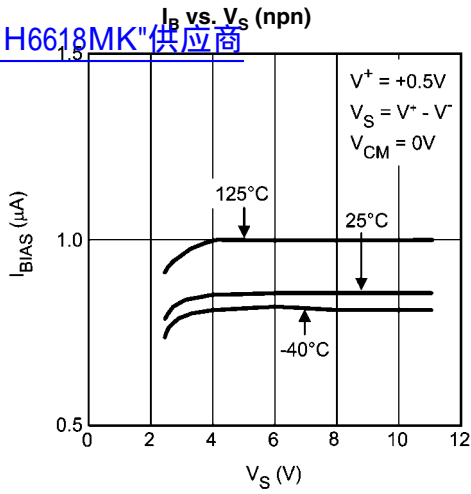
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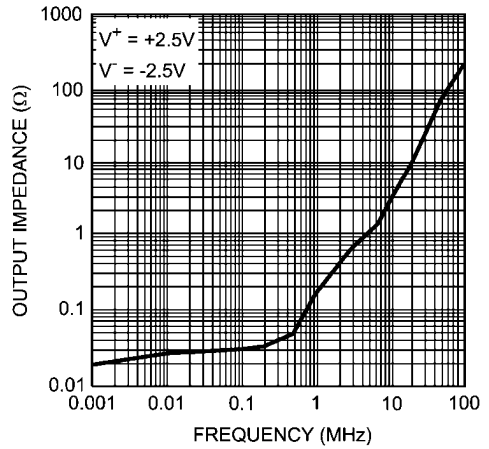
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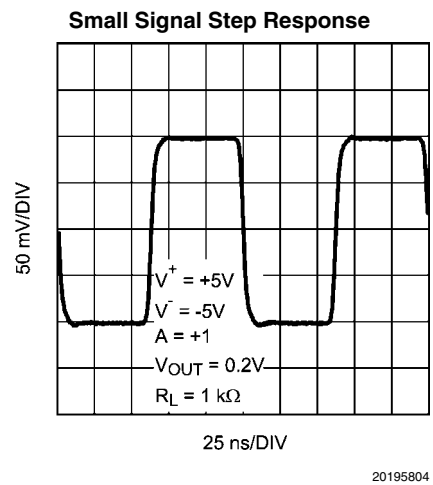
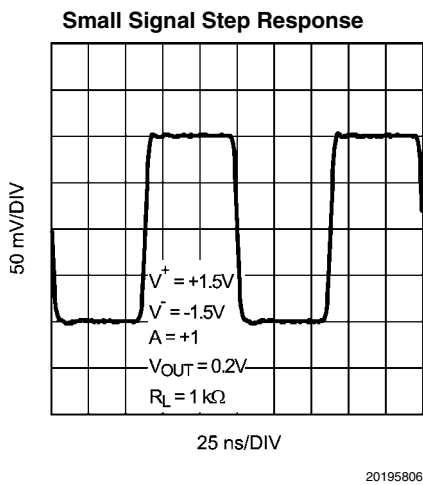
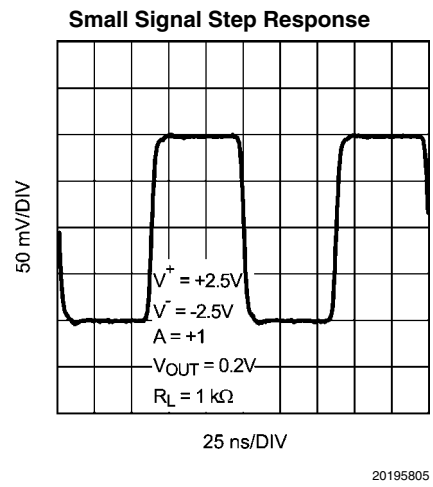
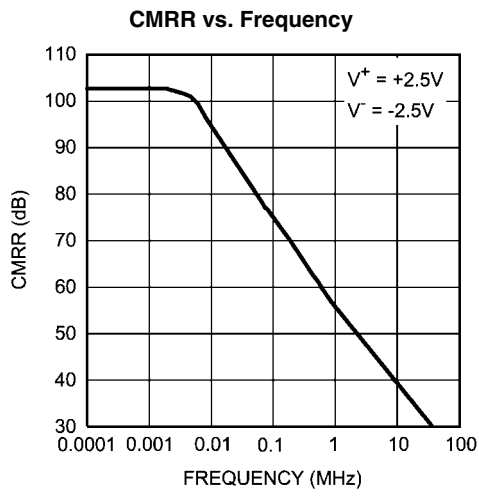
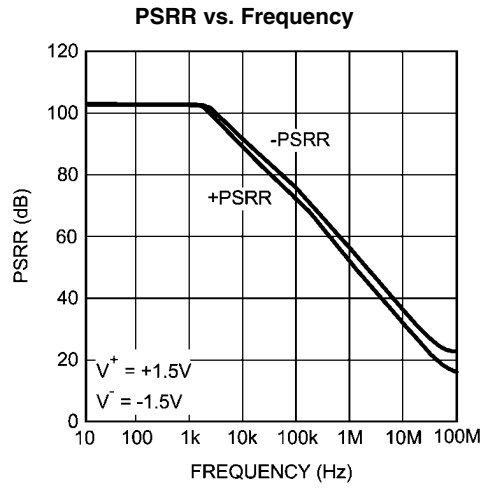
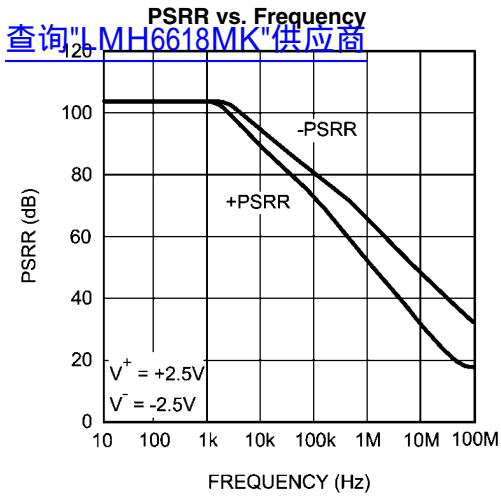


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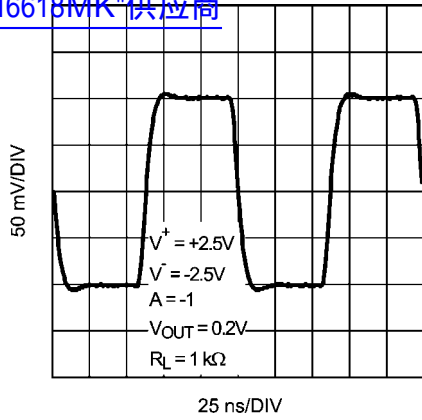


Closed Loop Output Impedance vs. Frequency A_V = +1



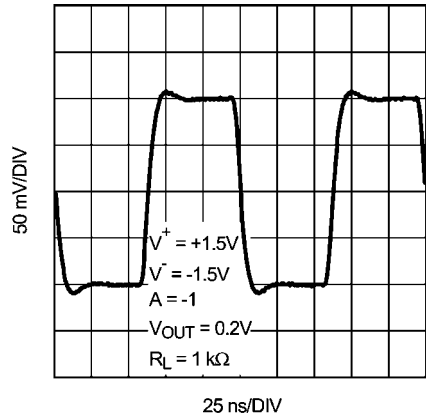


Small Signal Step Response
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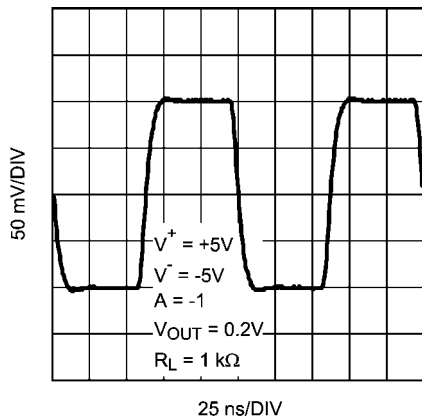
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Small Signal Step Response



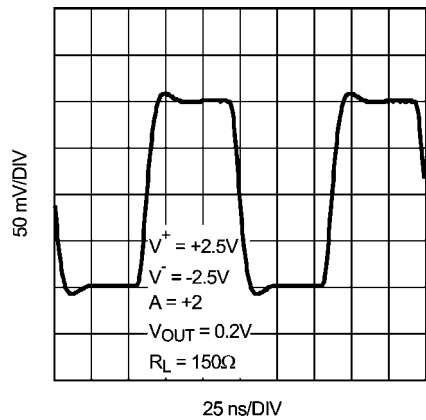
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Small Signal Step Response



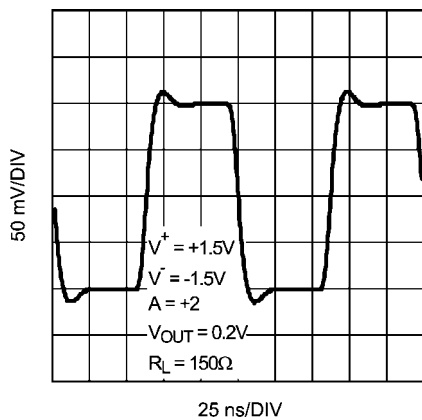
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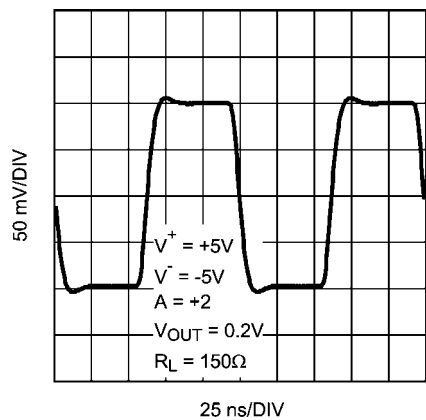
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Small Signal Step Response



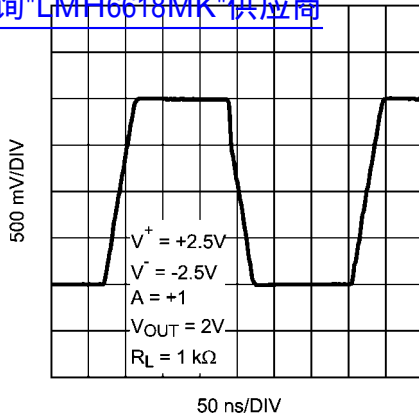
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Small Signal Step Response

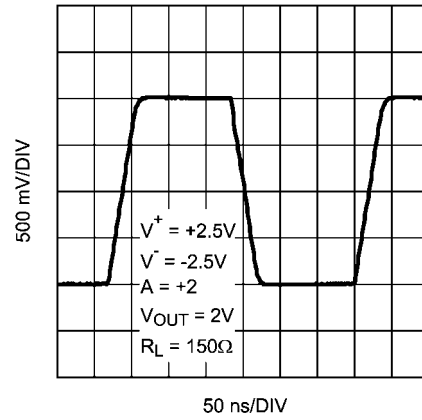


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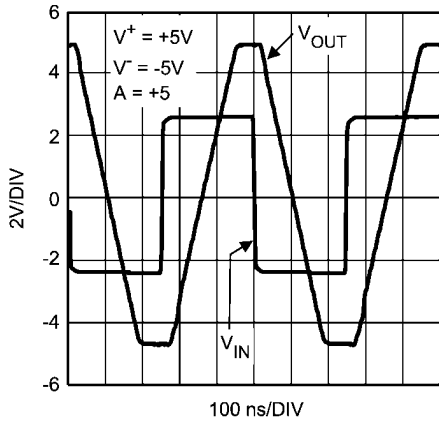
Large Signal Step Response
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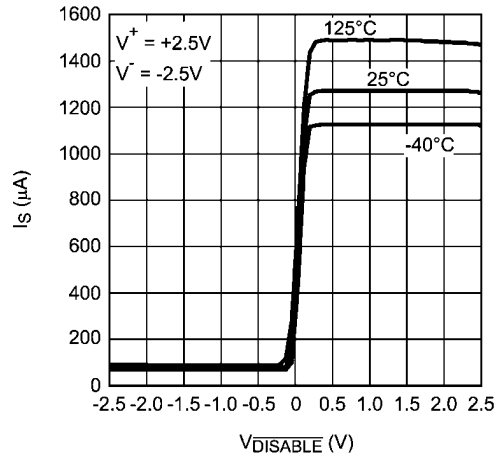
Large Signal Step Response



Overload Recovery Waveform



I_S vs. $V_{DISABLE}$



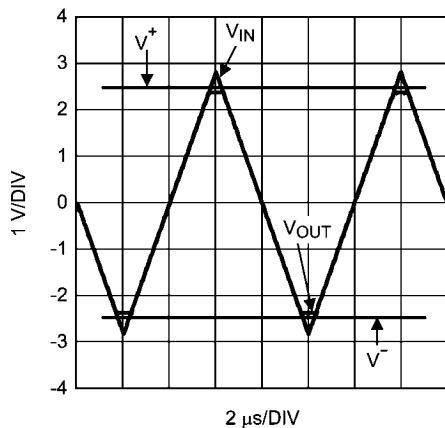
Application Information

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The LMH6618 is based on National Semiconductor's proprietary VIP10 dielectrically isolated bipolar process. This device family architecture features the following:

- Complimentary bipolar devices with exceptionally high f_t (~8GHz) even under low supply voltage (2.7V) and low bias current.
- Common emitter push-push output stage. This architecture allows the output to reach within millivolts of either supply rail.
- Consistent performance from any supply voltage (2.7V - 11V) with little variation with supply voltage for the most important specifications (e.g. BW, SR, I_{OUT} .)
- Significant power saving compared to competitive devices on the market with similar performance.

With 3V supplies and a common mode input voltage range that extends beyond either supply rail, the LMH6618 is well suited to many low voltage/low power applications. Even with 3V supplies, the -3 dB BW (at $A_V = +1$) is typically 120 MHz. The LMH6618 is designed to avoid output phase reversal. With input over-drive, the output is kept near the supply rail (or as close to it as mandated by the closed loop gain setting and the input voltage). *Figure 1* shows the input and output voltage when the input voltage significantly exceeds the supply voltages.



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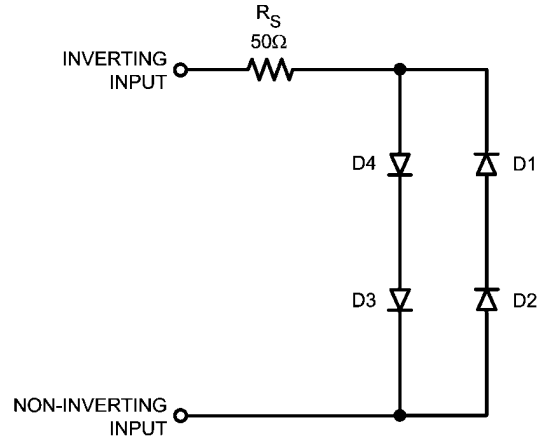
FIGURE 1. Input and Output Shown with CMVR Exceeded

If the input voltage range is exceeded by more than a diode drop beyond either rail, the internal ESD protection diodes will start to conduct. The current flow in these ESD diodes should be externally limited.

The LMH6618 can be shutdown by connecting the $\overline{\text{DISABLE}}$ pin to a voltage 0.5V below the supply midpoint

which will reduce the supply current to typically less than 100 μA . The $\overline{\text{DISABLE}}$ pin is "active low" and should be connected through a resistor to V^+ for normal operation. Shutdown is guaranteed when the $\overline{\text{DISABLE}}$ pin is 0.5V below the supply midpoint at any operating supply voltage and temperature.

In the shutdown mode, essentially all internal device biasing is turned off in order to minimize supply current flow and the output goes into high impedance mode. During shutdown, the input stage has an equivalent circuit as shown in *Figure 2*.



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FIGURE 2. Input Equivalent Circuit During Shutdown

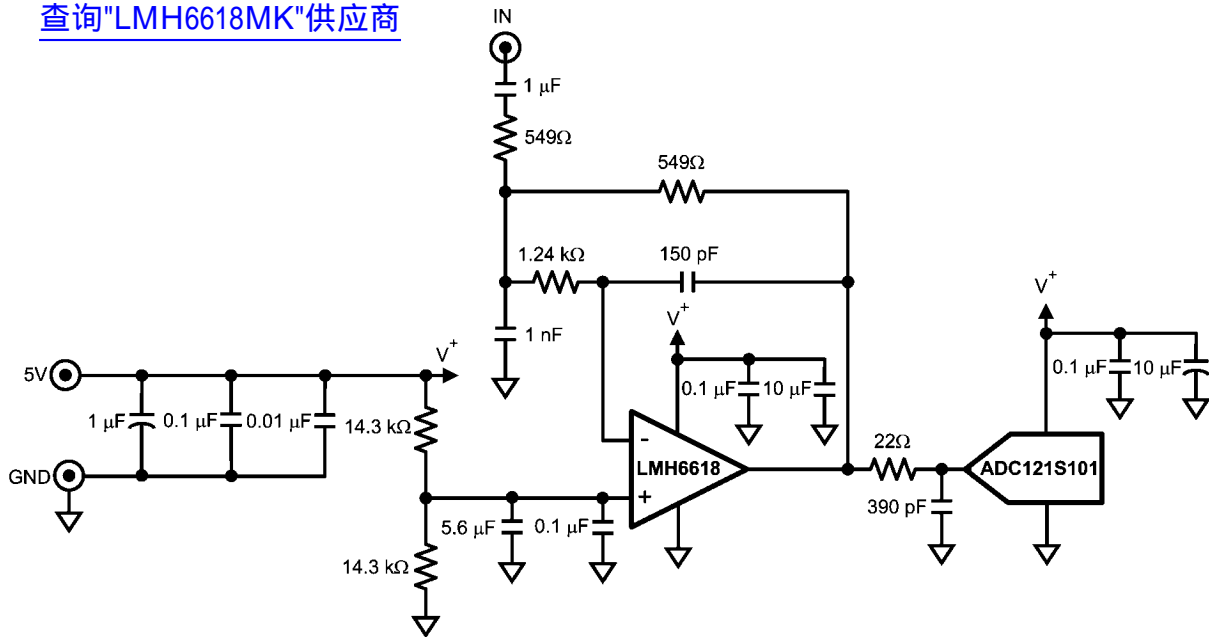
When the LMH6618 is shutdown, there may be current flow through the internal diodes shown, caused by input potential, if present. This current may flow through the external feedback resistor and result in an apparent output signal. In most shutdown applications the presence of this output is inconsequential. However, if the output is "forced" by another device, the other device will need to conduct the current described in order to maintain the output potential.

To keep the output at or near ground during shutdown when there is no other device to hold the output low, a switch using a transistor can be used to shunt the output to ground.

SINGLE CHANNEL ADC DRIVER

The low noise and wide bandwidth make the LMH6618 an excellent choice for driving a 12-bit ADC. *Figure 3* shows the schematic of the LMH6618 driving an ADC121S101. The ADC121S101 is a single channel 12-bit ADC. The LMH6618 is set up in a 2nd order multiple-feedback configuration with a gain of -1. The -3 dB point is at 500 kHz and the -0.01 dB point is at 100 kHz. *Table 1* shows the performance data of the LMH6618 and the ADC121S101.

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FIGURE 3. LMH6618 Driving an ADC121S101

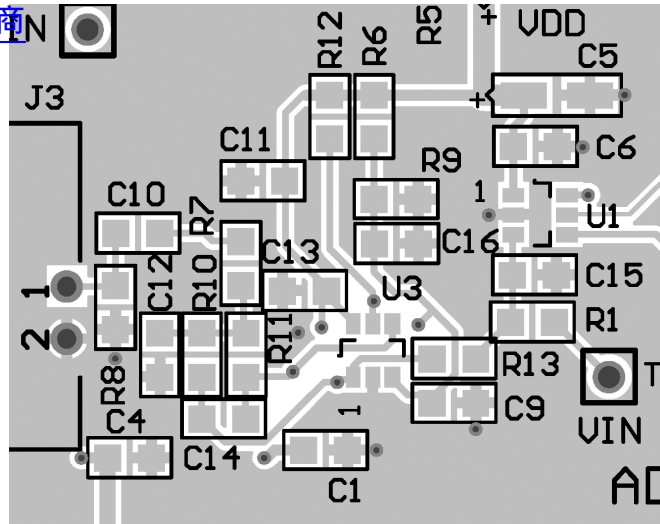
TABLE 1. Performance Data for the LMH6618 Driving an ADC121S101

Parameter	Measured Value
Signal Frequency	100 kHz
Signal Amplitude	4.5V
SINAD	71.5 dB
SNR	71.87 dB
THD	-82.4 dB
SFDR	90.97 dB
ENOB	11.6 bits

When the op amp and the ADC are using the same supply, it is important that both devices are well bypassed. A 0.1 μF ceramic capacitor and a 10 μF tantalum capacitor should be located as close as possible to each supply pin. A sample

layout is shown in *Figure 4*. The 0.1 μF capacitors (C13 and C6) and the 10 μF capacitors (C11 and C5) are located very close to the supply pins of the LMH6618 and the ADC121S101.

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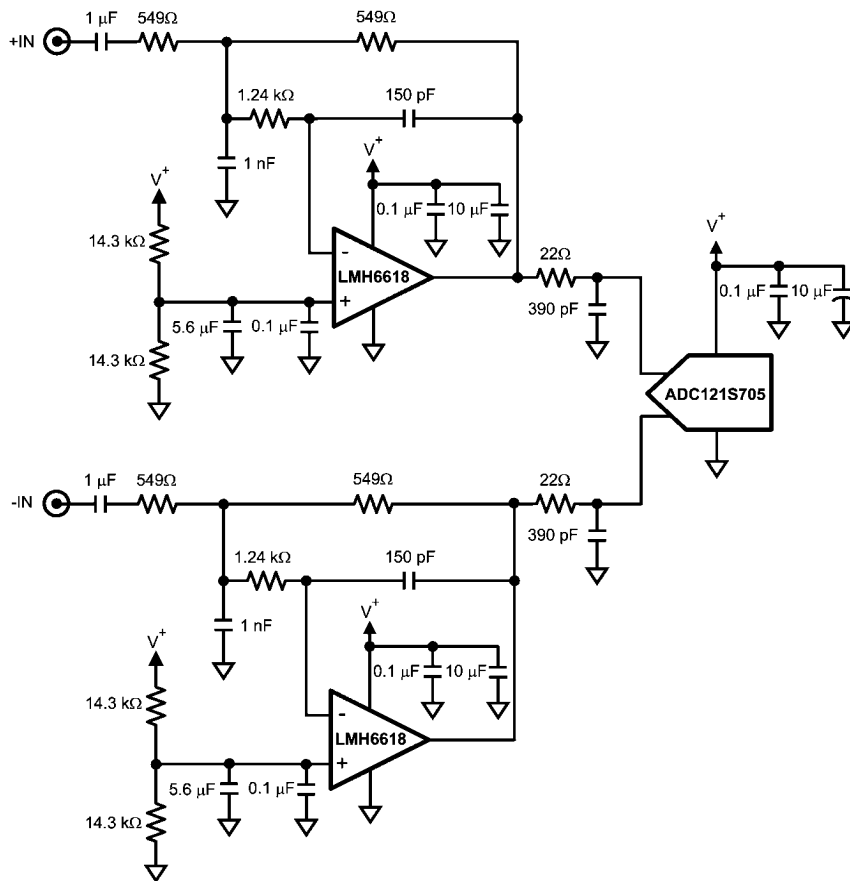
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FIGURE 4. LMH6618 and ADC121S101 Layout

DIFFERENTIAL ADC DRIVER

The circuit in *Figure 3* can be used to drive both inputs of a differential ADC. *Figure 5* shows the LMH6618 driving an AD-

C121S705. The ADC121S705 is a fully differential 12-bit ADC. Performance with this circuit is similar to the circuit in *Figure 3*.



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FIGURE 5. LMH6618 Driving an ADC121S705

DC LEVEL SHIFTING

Often a signal must be amplified and level shifted while using a single supply for the op amp. The circuit in *Figure 6* can do both of these tasks. The procedure for specifying the resistor values is as follows.

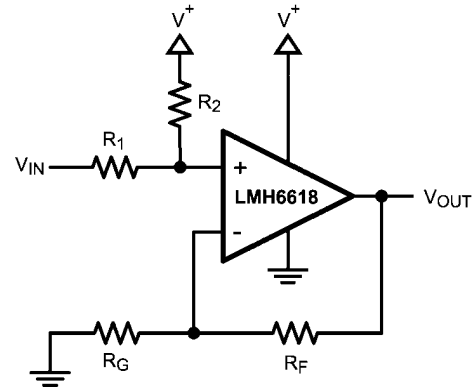
1. Determine the input voltage.
2. Calculate the input voltage midpoint, $V_{INMID} = V_{INMIN} + (V_{INMAX} - V_{INMIN})/2$.
3. Determine the output voltage needed.
4. Calculate the output voltage midpoint, $V_{OUTMID} = V_{OUTMIN} + (V_{OUTMAX} - V_{OUTMIN})/2$.
5. Calculate the gain needed, $gain = (V_{OUTMAX} - V_{OUTMIN}) / (V_{INMAX} - V_{INMIN})$.
6. Calculate the amount the voltage needs to be shifted from input to output, $\Delta V_{OUT} = V_{OUTMID} - gain \times V_{INMID}$.
7. Set the supply voltage to be used.
8. Calculate the noise gain, $noise\ gain = gain + \Delta V_{OUT}/V_S$.
9. Set R_F .
10. Calculate R_1 , $R_1 = R_F/gain$.
11. Calculate R_2 , $R_2 = R_F/(noise\ gain - gain)$.
12. Calculate R_G , $R_G = R_F/(noise\ gain - 1)$.

Check that both the V_{IN} and V_{OUT} are within the voltage ranges of the LMH6618.

The following example is for a V_{IN} of 0V to 1V with a V_{OUT} of 2V to 4V.

1. $V_{IN} = 0V$ to $1V$.
2. $V_{INMID} = 0V + (1V - 0V)/2 = 0.5V$.
3. $V_{OUT} = 2V$ to $4V$.
4. $V_{OUTMID} = 2V + (4V - 2V)/2 = 3V$.
5. $Gain = (4V - 2V)/(1V - 0V) = 2$
6. $\Delta V_{OUT} = 3V - 2 \times 0.5V = 2$.

7. For the example the supply voltage will be +5V.
8. Noise gain = $2 + 2/5V = 2.4$.
9. $R_F = 2\ k\Omega$
10. $R_1 = 2\ k\Omega/2 = 1\ k\Omega$
11. $R_2 = 2\ k\Omega/(2.4-2) = 5\ k\Omega$.
12. $R_G = 2\ k\Omega/(2.4 - 1) = 1.43\ k\Omega$.

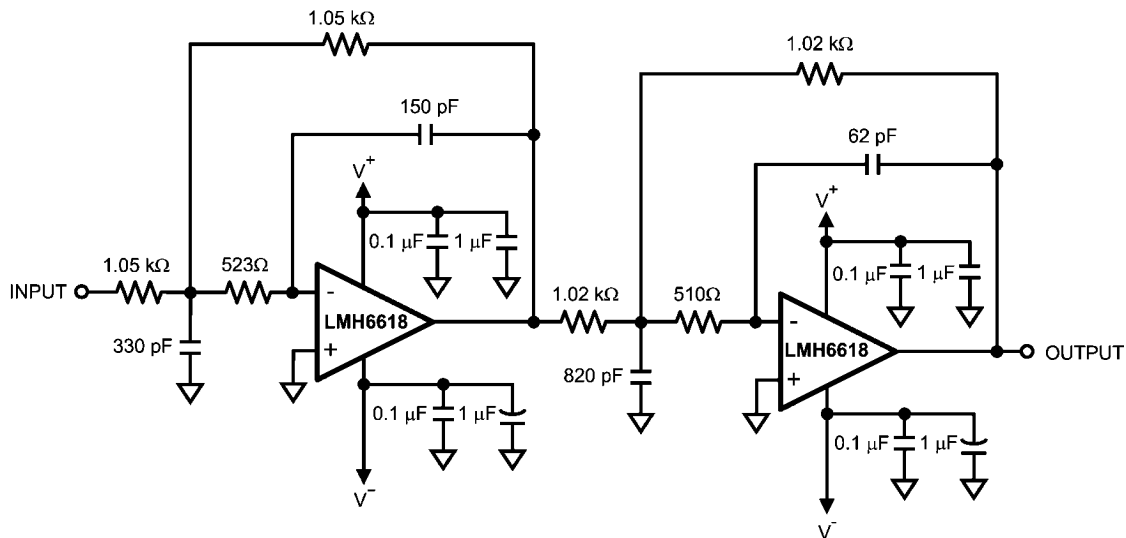


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FIGURE 6. DC Level Shifting

4th ORDER MULTIPLE FEEDBACK LOW-PASS FILTER

Figure 7 shows the LMH6618 used as the amplifier in a multiple feedback low-pass filter. This filter is set up to have a gain of +1 and a $-3\ dB$ point of 1 MHz. Values can be determined by using the WEBENCH® Active Filter Designer found at amplifiers.national.com.

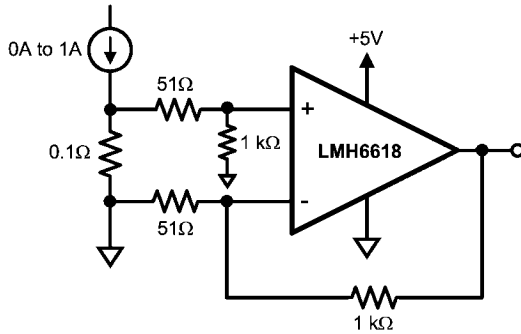


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FIGURE 7. 4th Order Multiple Feedback Low-Pass Filter

CURRENT SENSE AMPLIFIER

With its high input and output capability, low V_{OS} , and low I_B the LMH6618 is an ideal choice for a current sense amplifier application. Figure 8 shows the schematic of the LMH6618 set up in a low-side sense configuration which provides a conversion gain of 2V/A. Voltage error due to V_{OS} can be calculated to be $V_{OS} \times (1 + R_F/R_G)$ or $0.6 \text{ mV} \times 21 = 12.6 \text{ mV}$. Voltage error due to I_O is $I_O \times R_F$ or $0.26 \mu\text{A} \times 1 \text{ k}\Omega = 0.26 \text{ mV}$. Hence total voltage error is $12.6 \text{ mV} + 0.26 \text{ mV}$ or 12.86 mV which translates into a current error of $12.86 \text{ mV}/(2 \text{ V/A}) = 6.43 \text{ mA}$.

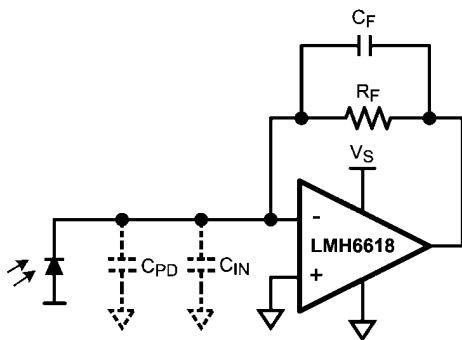


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FIGURE 8. Current Sense Amplifier

TRANSIMPEDANCE AMPLIFIER

By definition, a photodiode produces either a current or voltage output from exposure to a light source. A Transimpedance Amplifier (TIA) is utilized to convert this low-level current to a usable voltage signal. The TIA often will need to be compensated to insure proper operation.



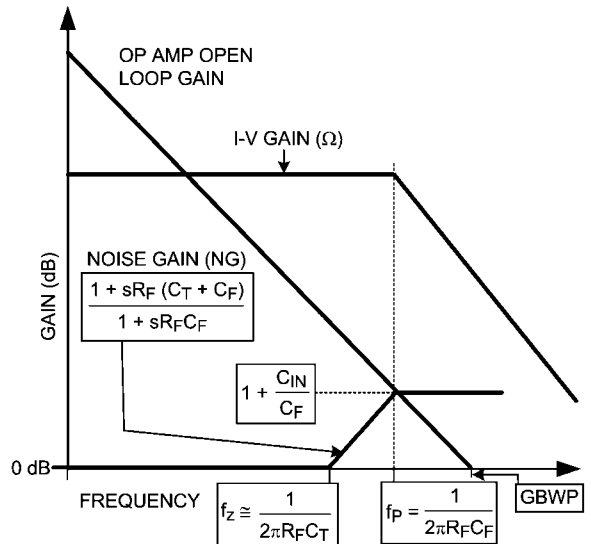
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FIGURE 9. Photodiode Modeled with Capacitance Elements

Figure 9 shows the LMH6618 modeled with photodiode and the internal op amp capacitances. The LMH6618 allows circuit operation of a low intensity light due to its low input bias current by using larger values of gain (R_F). The total capacitance (C_T) on the inverting terminal of the op amp includes the photodiode capacitance (C_{PD}) and the input capacitance of the op amp (C_{IN}). This total capacitance (C_T) plays an important role in the stability of the circuit. The noise gain of this circuit determines the stability and is defined by:

$$NG = \frac{1 + sR_F (C_T + C_F)}{1 + sC_F R_F} \tag{1}$$

$$\text{Where, } f_z \cong \frac{1}{2\pi R_F C_T} \text{ and } f_p = \frac{1}{2\pi R_F C_F} \tag{2}$$



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FIGURE 10. Bode Plot of Noise Gain Intersecting with Op Amp Open-Loop Gain

Figure 10 shows the bode plot of the noise gain intersecting the op amp open loop gain. With larger values of gain, C_T and R_F create a zero in the transfer function. At higher frequencies the circuit can become unstable due to excess phase shift around the loop.

A pole at f_p in the noise gain function is created by placing a feedback capacitor (C_F) across R_F . The noise gain slope is flattened by choosing an appropriate value of C_F for optimum performance.

Theoretical expressions for calculating the optimum value of C_F and the expected -3 dB bandwidth are:

$$C_F = \sqrt{\frac{C_T}{2\pi R_F (GBWP)}} \tag{3}$$

$$f_{-3 \text{ dB}} = \sqrt{\frac{GBWP}{2\pi R_F C_T}} \tag{4}$$

Equation 4 indicates that the -3 dB bandwidth of the TIA is inversely proportional to the feedback resistor. Therefore, if the bandwidth is important then the best approach would be to have a moderate transimpedance gain stage followed by a broadband voltage gain stage.

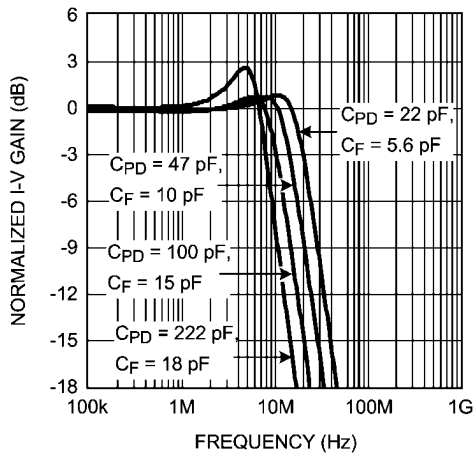
Table 2 shows the measurement results of the LMH6618 with different photodiodes having various capacitances (C_{PD}) and a feedback resistance (R_F) of $1 \text{ k}\Omega$.

TABLE 2. TIA (Figure 1) Compensation and Performance Results
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C_{PD} (pF)	C_T (pF)	$C_{F\text{ CAL}}$ (pF)	$C_{F\text{ USED}}$ (pF)	$f_{-3\text{ dB CAL}}$ (MHz)	$f_{-3\text{ dB MEAS}}$ (MHz)	Peaking (dB)
22	24	7.7	5.6	23.7	20	0.9
47	49	10.9	10	16.6	15.2	0.8
100	102	15.8	15	11.5	10.8	0.9
222	224	23.4	18	7.81	8	2.9

Note:
 GBWP = 65 MHz
 $C_T = C_{PD} + C_{IN}$
 $C_{IN} = 2\text{ pF}$
 $V_S = \pm 2.5\text{ V}$

Figure 11 shows the frequency response for the various photodiodes in Table 2.

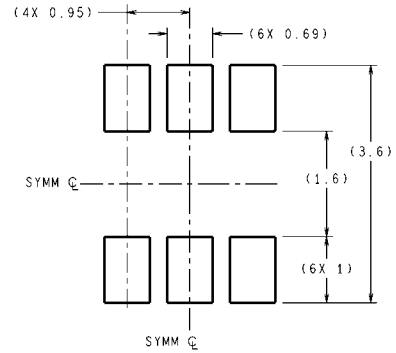
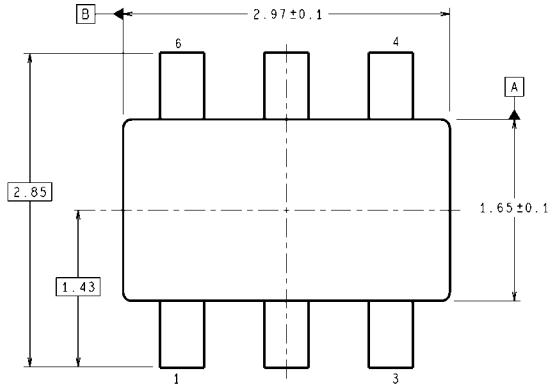


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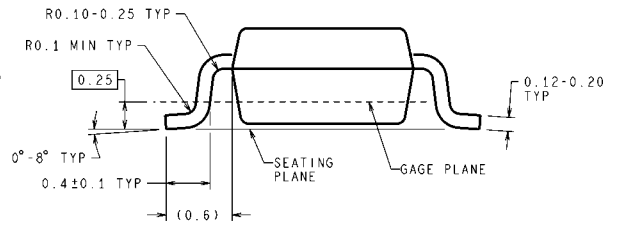
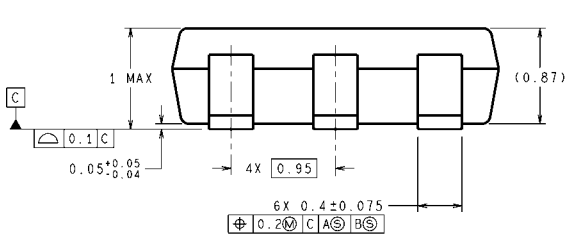
FIGURE 11. Frequency Response for Various Photodiode and Feedback Capacitors

When analyzing the noise at the output of the TIA, it is important to note that the various noise sources (i.e. op amp noise voltage, feedback resistor thermal noise, input noise current, photodiode noise current) do not all operate over the same frequency band. Therefore, when the noise at the output is calculated, this should be taken into account. The op amp noise voltage will be gained up in the region between the noise gain's zero and pole (f_Z and f_P in Figure 10). The higher the values of R_F and C_T , the sooner the noise gain peaking starts and therefore its contribution to the total output noise will be larger. It is obvious to note that it is advantageous to minimize C_{IN} by proper choice of op amp or by applying a reverse bias across the diode at the expense of excess dark current and noise.

Physical Dimensions inches (millimeters) unless otherwise noted
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RECOMMENDED LAND PATTERN



DIMENSIONS ARE IN MILLIMETERS

MK06A (Rev D)

**6-Pin TSOT23
 NS Package Number MK06A**

Notes

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